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As Cont.	9. (Amended) A micro-hotplate device according to claim 1, wherein the	
	semiconducting material in the island is silicon.	
	10. (Amended) A micro-hotplate device according to claim 1, wherein the	
	semiconducting material in the island is silicon carbide.	
	11. (Amended) A micro-hotplate device according to claim 1, wherein the support	
	substrate and the island are made of the same material.	
	17. (Amended) A method according to claim 12, wherein at least one of said etching	L
	steps is an anisotropic potassium hydroxide etching step.	
	18. (Amended) A method according to claim 12, wherein at least one of said etching	
8	steps is an anisotropic tetramethyl ammonium hydroxide etching step.	
	19. (Amended) A method according to claim 12, wherein at least one of said etching	
	steps is a deep reactive ion etching step.	
	20. (Amended) A micro-hotplate device according to claim 1, wherein one or several of	
	the chemical sensors utilize the field-effect detection mechanism.	
T & .	22. (Amended) A micro-hotplate device according to claim 1, wherein one or several of	
	the chemical sensors are operated as gas sensors.	
	23. (Amended) A micro-hotplate device according to claim 21, wherein one or several	
	field-effect gas sensors are combined with one or several gas sensors that utilize resistance	
	changes as detection mechanism.	
64	26. (Amended) A micro-hotplate device according to claim 1, wherein the support	
HAYES, SOLOWAY,	substrate contains an array of several islands.	
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